

65V N-Ch Power MOSFET

| | | | |
|------------------|--------------|-----|---|
| V_{DS} | | 65 | V |
| $R_{DS(on),typ}$ | $V_{GS}=10V$ | 2.5 | m |

174 A

65
±20 V

Pulsed Drain Current I_{DM} 400 A

Operating and Storage Temperature P_D 172 W
 T_J, T_{stg} -55 to 175

Absolute Maximum Ratings

| Parameter | Symbol | Max | Unit |
|-------------------------------------|----------|------|------|
| Thermal Resistance Junction-Ambient | R_{JA} | 60 | °C/W |
| Thermal Resistance Junction-Case | R_{JC} | 0.87 | °C/W |

Electrical Characteristics at $T_J=25^\circ\text{C}$ (unless otherwise specified)

Static Characteristics

| | | | | | | |
|--------------------------------|--------------|---|---|-----|-----------|---|
| Gate to Source Leakage Current | I_{GSS} | $V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$ | - | - | ± 100 | |
| Drain to Source on Resistance | $R_{DS(on)}$ | $V_{GS}=10\text{V}, I_D=20\text{A}$ | - | 2.5 | 3 | m |
| Drain to Source on Resistance | $R_{DS(on)}$ | $V_{GS}=4.5\text{V}, I_D=20\text{A}$ | - | 3.6 | | m |
| Gate Resistance | R_G | | - | | | |

Dynamic Characteristics

| | | | | | | |
|-------------------------------|-------------------|--|---|------|---|----|
| Input Capacitance | C_{iss} | | | | | |
| Output Capacitance | C_{oss} | $V_{GS}=0\text{V}, V_{DS}=30\text{V}, f=1\text{MHz}$ | | 1625 | | |
| Reverse Transfer Capacitance | C_{rss} | | | | | |
| Total Gate Charge | $Q_g(10\text{V})$ | | - | | - | |
| Gate to Source Charge | Q_{gs} | $V_{DD}=30\text{V}, I_D=20\text{A}, V_{GS}=10\text{V}$ | - | 34 | - | nC |
| Gate to Drain (Miller) Charge | Q_{gd} | | - | 8 | - | |
| | | | | 14 | | |
| | | | | 13 | - | |
| | | | | 49 | - | ns |
| | | | | 19 | | |

| | |
|--|---|
| Fig 1. Typical Output Characteristics | Figure 2. On-Resistance vs. Gate-Source Voltage |
| Figure 3. On-Resistance vs. Drain Current and Gate Voltage | Figure 4. Normalized On-Resistance vs. Junction Temperature |
| Figure 5. Typical Transfer Characteristics | Figure 6. Typical Source-Drain Diode Forward Voltage |

Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

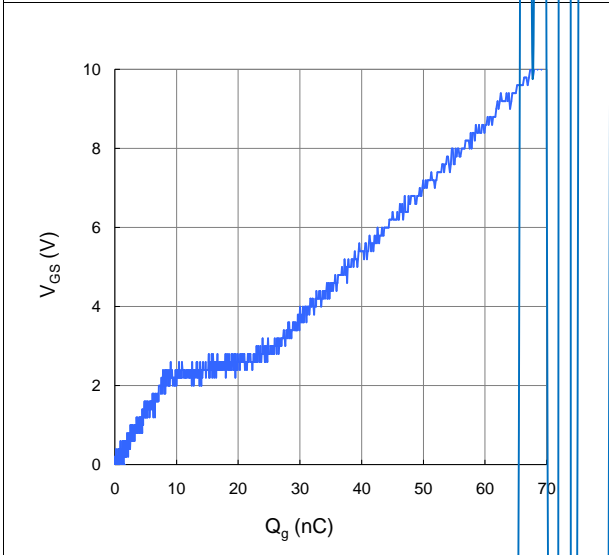


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

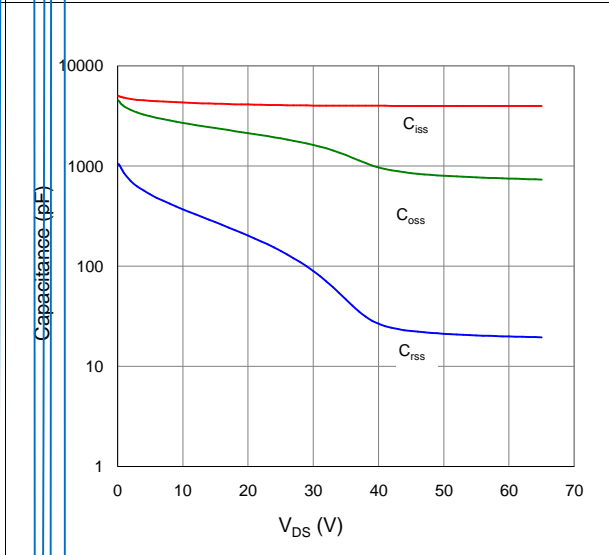


Figure 9. Maximum Safe Operating Area

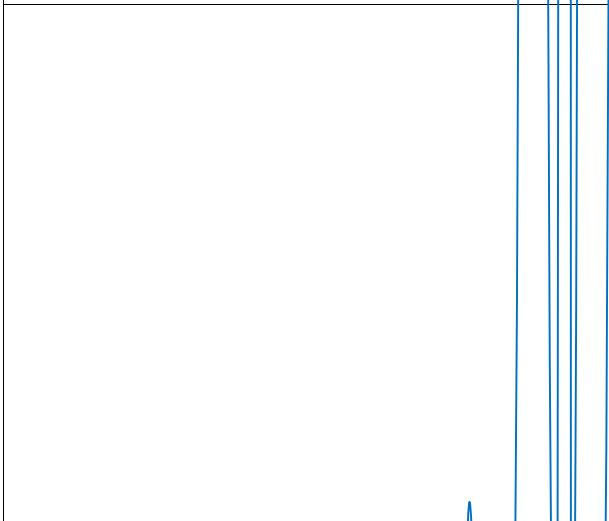


Figure 10. Maximum Drain Current vs. Case Temperature

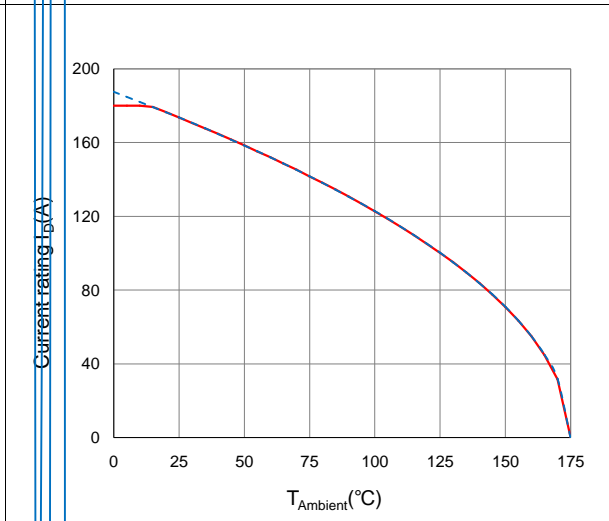
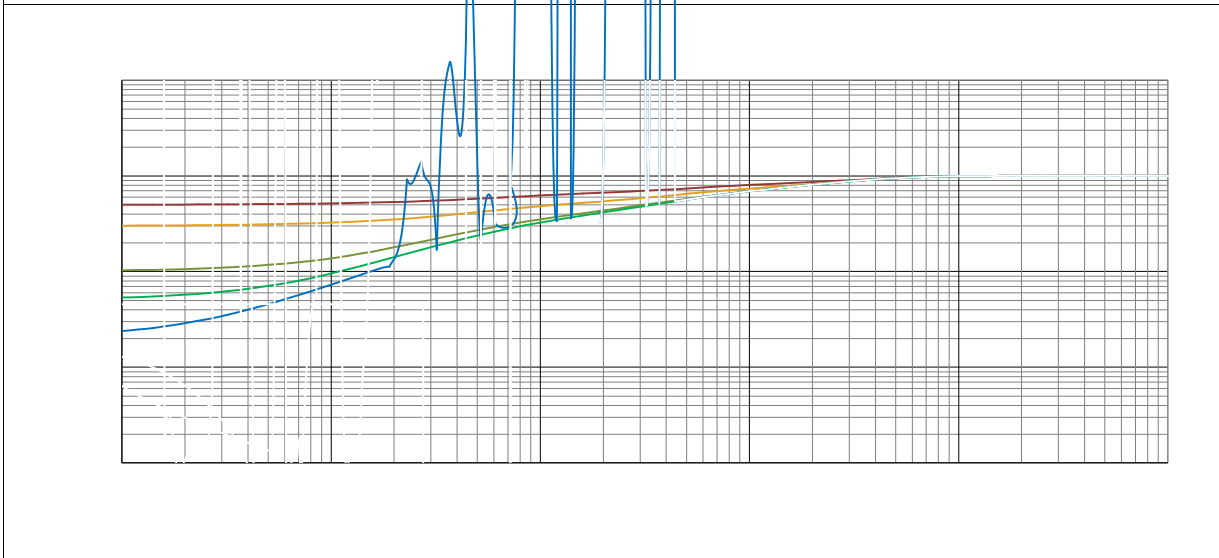
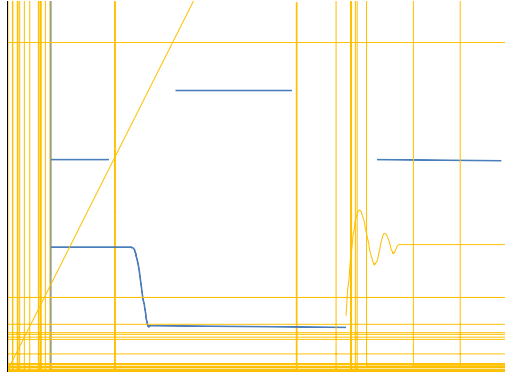
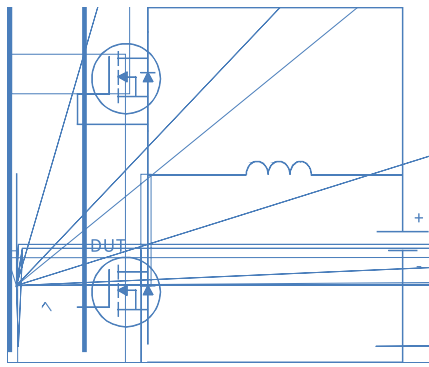


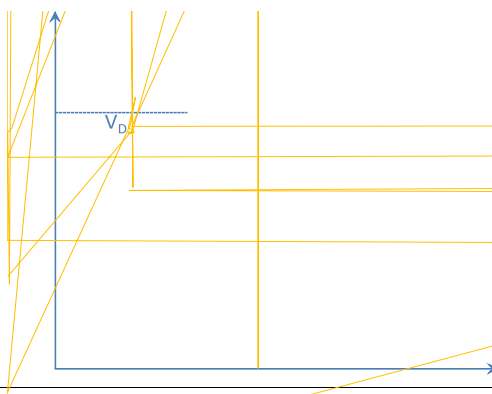
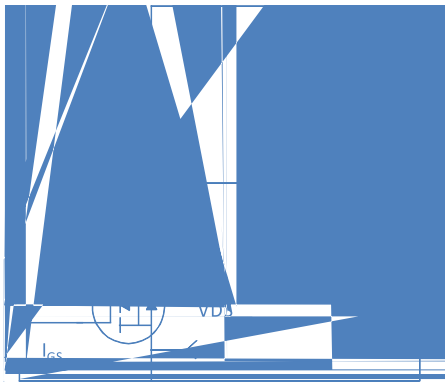
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient



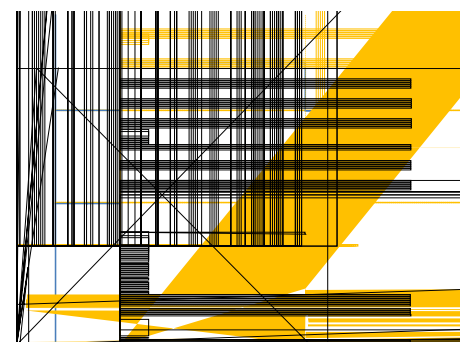
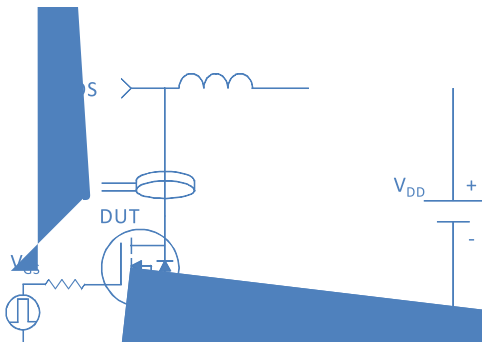
Inductive switching Test



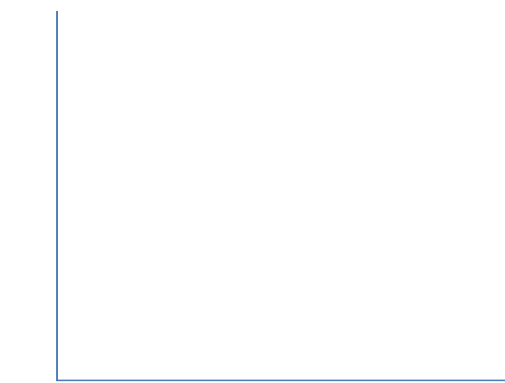
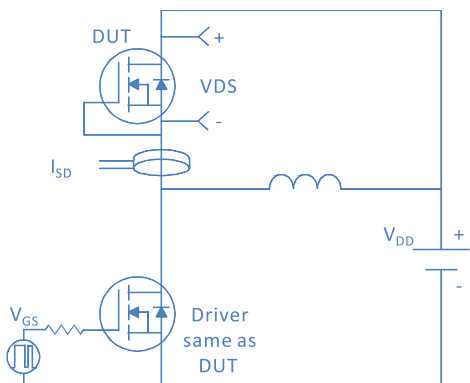
Gate Charge Test



Uclamped Inductive Switching (UIS) Test

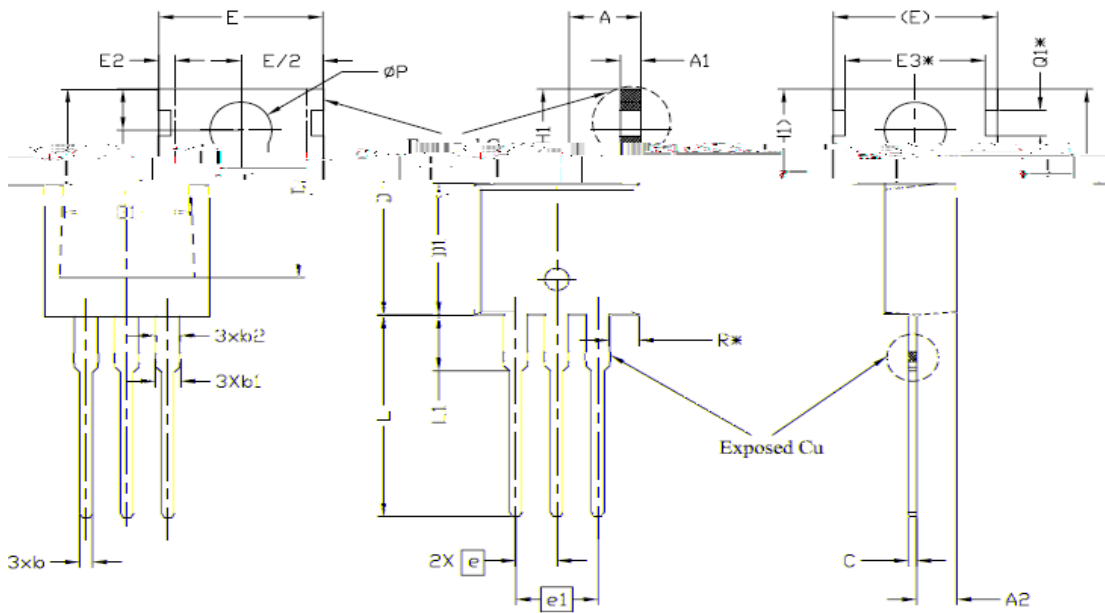


Diode Recovery Test



Package Outline

TO-220, 3 leads



| SYMBOL | DIMENSIONS | | | NOTES |
|------------|------------|-------|-------|-------|
| | MIN. | NOM. | MAX. | |
| A1 | 1.14 | 1.27 | 1.40 | 1 |
| A2 | 2.54 | 2.67 | 2.80 | 1 |
| E | 6.35 | 6.35 | 6.35 | 1 |
| E1 | 1.27 | 1.27 | 1.27 | 1 |
| E2 | 1.27 | 1.27 | 1.27 | 1 |
| e | 0.48 | 0.50 | 0.50 | 1 |
| C | 14.70 | 14.97 | 15.00 | 4 |
| A | 3.30 | 3.30 | 3.30 | 1 |
| ØP | 10.66 | 10.66 | 10.66 | 2 |
| Ø1 | 3.68 | 3.68 | 3.68 | 3,5 |
| R* | 0.50 | 0.75 | 0.80 | 2 |
| 3xb | | 3.78 | 3.78 | 2 |
| 3xb1 | | 2.99 | 2.99 | 2 |
| 3xb2 | | 6.08 | 6.08 | 2 |
| 2X e | | 1.00 | 1.00 | 2 |
| e1 | | 1.27 | 1.27 | 2 |
| Exposed Cu | | 1.27 | 1.27 | 2 |